

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

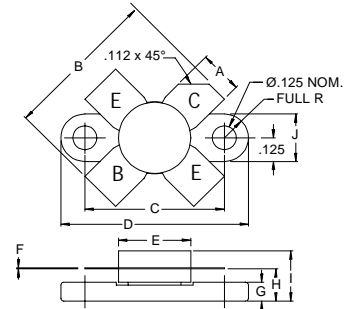
The **ASI BLW83** is Designed for use in transmitting amplifiers operating in the h.f. and v.h.f. bands and for applications as linear amplifier in class-A and AB.

FEATURES:

- $P_G = 20$ dB min. at 10 W/30 MHz
- $IMD_3 = -30$ dBc max. at 10 W(PEP)
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	3.0 A
V_{CES}	65 V
V_{CEO}	36 V
V_{EBO}	4.0 V
P_{DISS}	80 W @ $T_C = 25$ °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	2.2 °C/W

PACKAGE STYLE .380 4L FLG


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.785 / 19.94	
C	.720 / 18.29	.730 / 18.54
D	.970 / 24.64	.980 / 24.89
E		.385 / 9.78
F	.004 / 0.10	.006 / 0.15
G	.085 / 2.16	.105 / 2.67
H	.160 / 4.06	.180 / 4.57
I		.280 / 7.11
J	.240 / 6.10	.255 / 6.48

CHARACTERISTICS $T_C = 25$ °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CES}	$I_C = 10$ mA	65			V
BV_{CEO}	$I_C = 50$ mA	36			V
BV_{EBO}	$I_E = 10$ mA	4.0			V
I_{CES}	$V_{CE} = 36$ V			5	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 1.25$ A	10		100	---
C_{ob}	$V_{CB} = 12.5$ V $f = 1.0$ MHz		100		pF
G_{PE}	$V_{CC} = 26$ V $I_{CQ} = 25$ mA $f = 30$ MHz	20	21	---	dB
IMD_3	$P_{OUT} = 10$ W(PEP)		-30		dB